American Microsemiconductor 1N4830 Technical Specifications Diodes > Forward Reference Diodes Α Α L D_2 ь Α \mathbf{D}_1 D_2 25.400 4.440 0.457/0.559 2.030 mm 1.000 0.175 0.018/0.022 0.080 inches

- Hermetically Sealed Glass Package DO-35
- High Reverse Breakdown and Low Leakage
- Excellent Low Voltage Regulation
- Planar Passivated Die Elements

	Value	Unit
Military / High Rel	N	
@ I_{R} Test Cond.		mA
$V_{\mbox{\scriptsize FM}}$ Max. Forward Voltage	2.7	V
@ I_{FM} Test Cond.	100	mA
@ I_{RM} Max. Rev. Current	100	nA
@ V_{R} Test Cond.	20	V
Semiconductor Material	Silicon	
Package Style	DO-35	
Mounting Style	Any	

axial lead diodes These represent configurations of one to four p-n junctions in series which may be used in any application requiring tight tolerance, low voltage levels versus current. This method of low voltage regulation is comparatively superior in dynamic impedence than low voltage zeners where tunneling instead of avalanche current is dominant. Typical applications include use as signal limiters, level shifters in transistor logic, meter protectors, and low voltage regulators.

